

SIPMOS® Small-Signal-Transistor
Features

- N-channel
- Enhancement mode
- Logic level
- dv/dt rated
- Pb-free lead-plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen free according to IEC61249-2-21

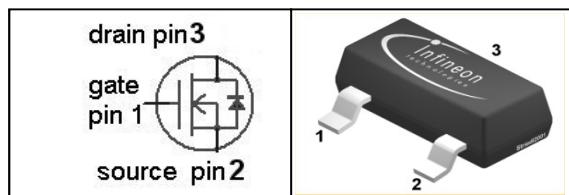


Halogen-Free

Product Summary

V_{DS}	60	V
$R_{DS(on),max}$	3.5	Ω
I_D	0.23	A

PG-SOT-23



Type	Package	Tape and Reel	Marking
BSS138N	PG-SOT-23	H6327: 3000	SKs
BSS138N	PG-SOT-23	H6433: 10000	SKs

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_A=25\text{ }^\circ\text{C}$	0.23	A
		$T_A=70\text{ }^\circ\text{C}$	0.18	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ }^\circ\text{C}$	0.92	
Reverse diode dv/dt	dv/dt	$I_D=0.23\text{ A}$, $V_{DS}=48\text{ V}$, $di/dt=200\text{ A}/\mu\text{s}$, $T_{j,max}=150\text{ }^\circ\text{C}$	6	kV/ μs
Gate source voltage	V_{GS}		± 20	V
ESD sensitivity		JESD22-A114 (HBM)	Class 0 (<250V)	
Power dissipation	P_{tot}	$T_A=25\text{ }^\circ\text{C}$	0.36	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - minimal footprint	R_{thJA}		-	-	350	K/W
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Electrical characteristics, at $T_j=25$ °C, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0$ V, $I_D=250$ µA	60	-	-	V
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=26$ µA	0.6	1.0	1.4	
Drain-source leakage current	I_D (off)	$V_{\text{DS}}=60$ V, $V_{\text{GS}}=0$ V, $T_j=25$ °C	-	-	0.1	µA
		$V_{\text{DS}}=60$ V, $V_{\text{GS}}=0$ V, $T_j=150$ °C	-	-	5	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20$ V, $V_{\text{DS}}=0$ V	-	1	10	nA
Drain-source on-state resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=4.5$ V, $I_D=0.03$ A	-	3.3	4.0	Ω
		$V_{\text{GS}}=4.5$ V, $I_D=0.19$ A	-	3.5	6.0	
		$V_{\text{GS}}=10$ V, $I_D=0.23$ A	-	2.2	3.5	
Transconductance	g_{fs}	$ V_{\text{DS}} >2 I_D R_{\text{DS}(\text{on})\text{max}}$, $I_D=0.18$ A	0.1	0.2	-	s

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0 \text{ V}, V_{DS}=25 \text{ V}, f=1 \text{ MHz}$	-	32	41	pF
Output capacitance	C_{oss}		-	7.2	9.5	
Reverse transfer capacitance	C_{rss}		-	2.8	3.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30 \text{ V}, V_{GS}=10 \text{ V}, I_D=0.23 \text{ A}, R_G=6 \Omega$	-	2.3	3.5	ns
Rise time	t_r		-	3.0	4.5	
Turn-off delay time	$t_{d(off)}$		-	6.7	10	
Fall time	t_f		-	8.2	12.3	

Gate Charge Characteristics

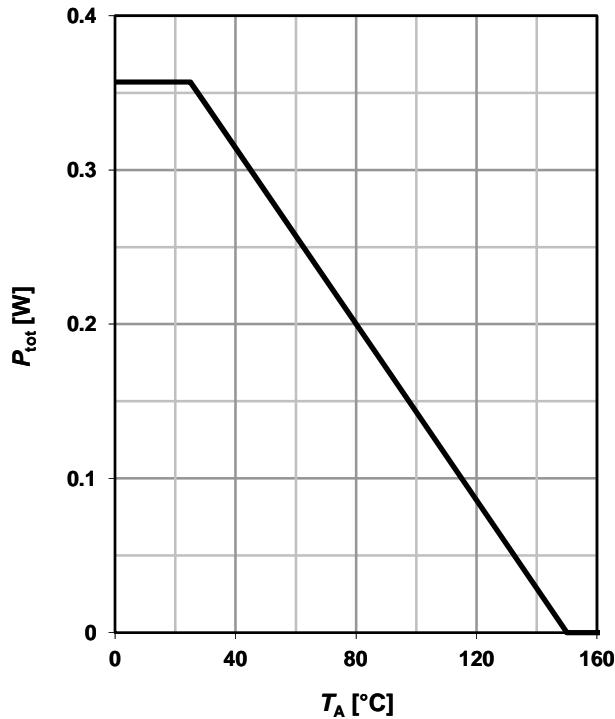
Gate to source charge	Q_{gs}	$V_{DD}=48 \text{ V}, I_D=0.23 \text{ A}, V_{GS}=0 \text{ to } 10 \text{ V}$	-	0.10	0.14	nC
Gate to drain charge	Q_{gd}		-	0.3	0.4	
Gate charge total	Q_g		-	1.0	1.4	
Gate plateau voltage	$V_{plateau}$		-	3.3	-	V

Reverse Diode

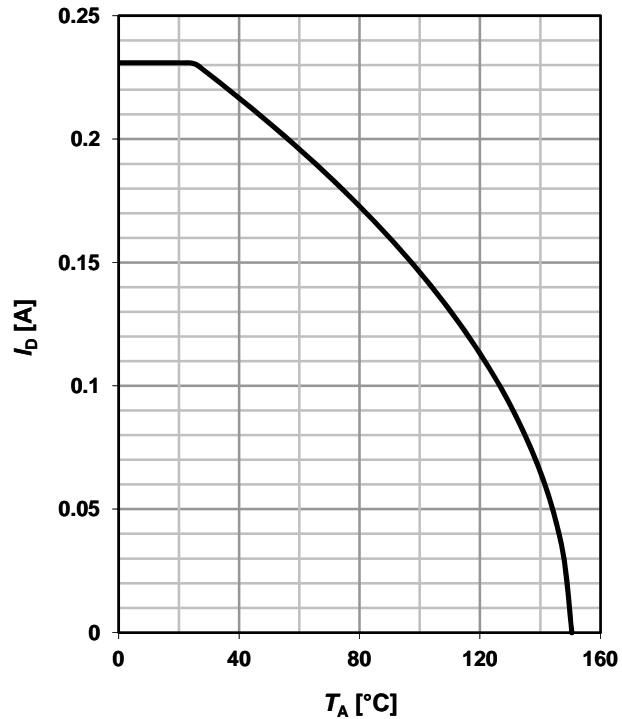
Diode continuous forward current	I_S	$T_A=25 \text{ }^\circ\text{C}$	-	-	0.23	A
Diode pulse current	$I_{S,pulse}$		-	-	0.92	
Diode forward voltage	V_{SD}	$V_{GS}=0 \text{ V}, I_F=0.23 \text{ A}, T_j=25 \text{ }^\circ\text{C}$	-	0.83	1.2	V
Reverse recovery time	t_{rr}	$V_R=30 \text{ V}, I_F=0.23 \text{ A}, di_F/dt=100 \text{ A}/\mu\text{s}$	-	9.1	14.5	ns
Reverse recovery charge	Q_{rr}		-	3.3	5	nC

1 Power dissipation

$$P_{\text{tot}} = f(T_A)$$

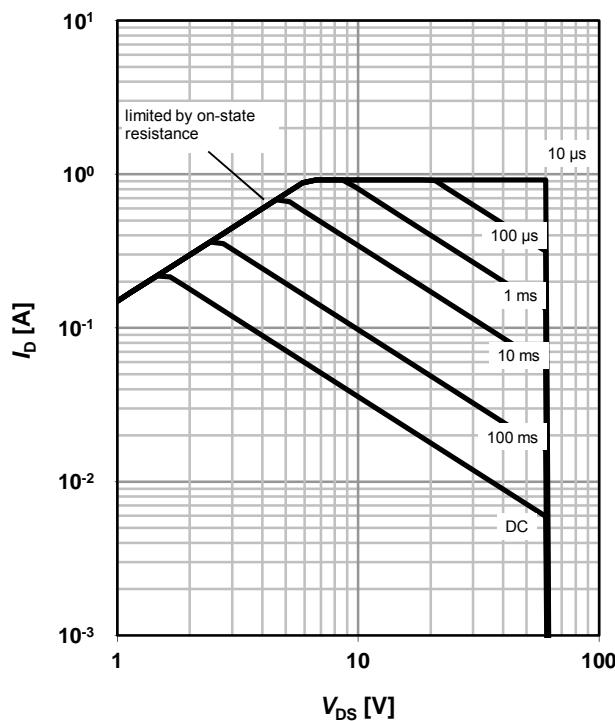

2 Drain current

$$I_D = f(T_A); V_{GS} \geq 10 \text{ V}$$


3 Safe operating area

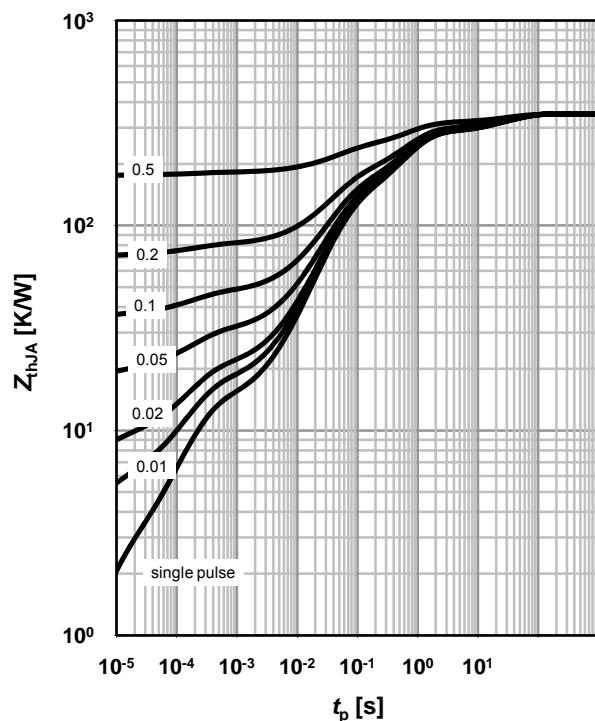
$$I_D = f(V_{DS}); T_A = 25 \text{ °C}; D = 0$$

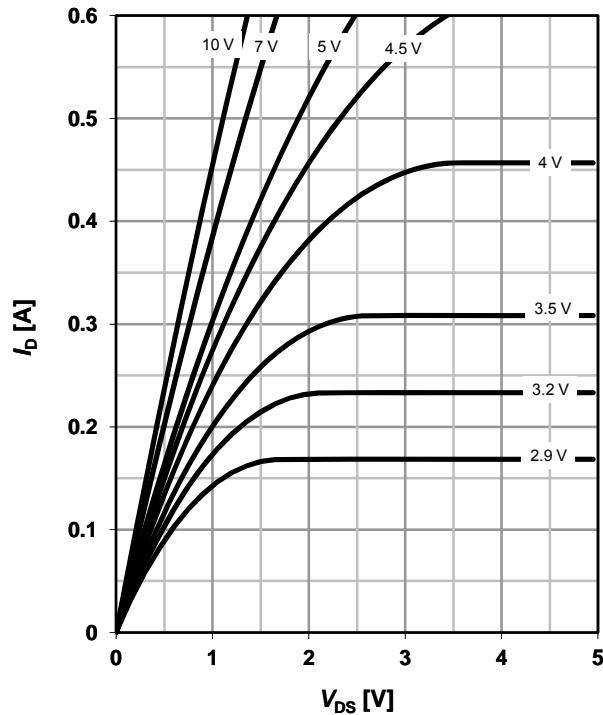
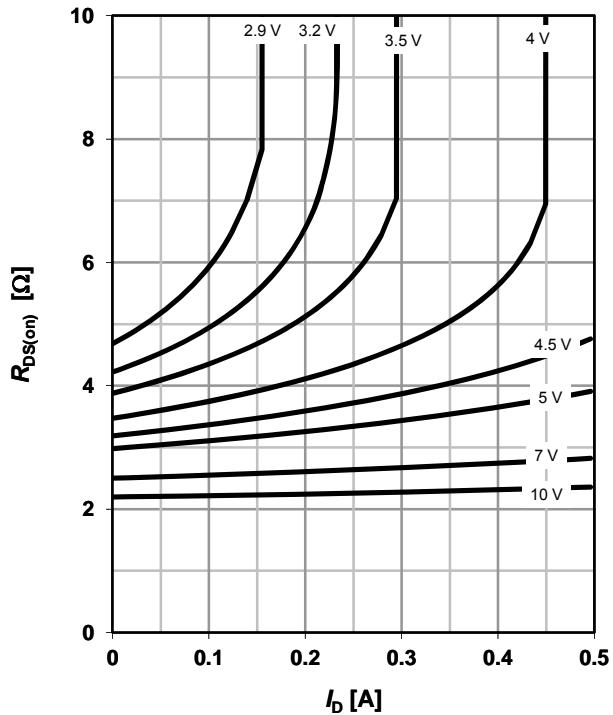
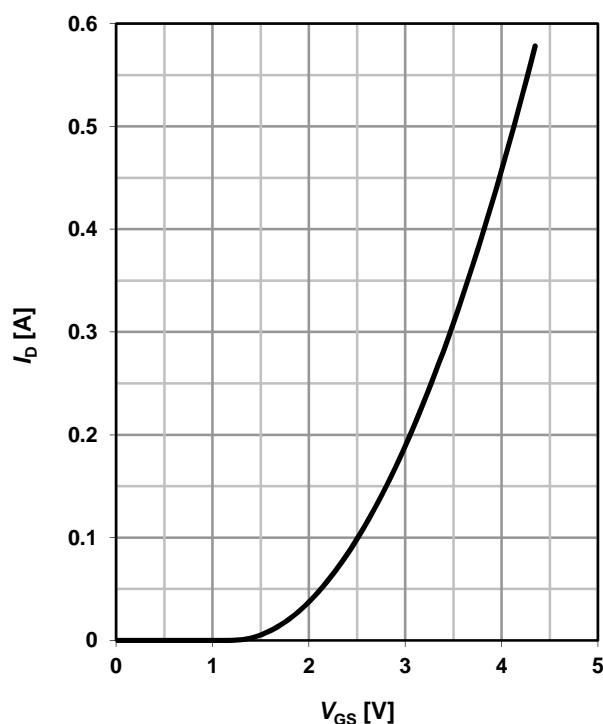
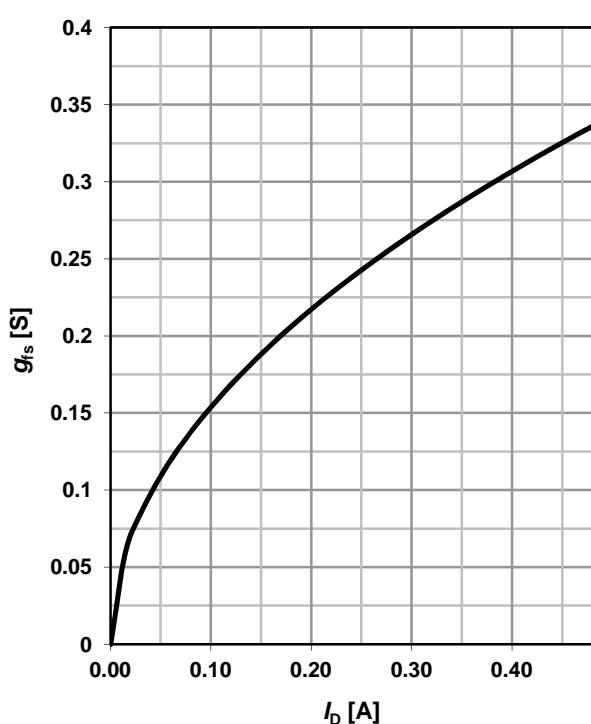
parameter: t_p

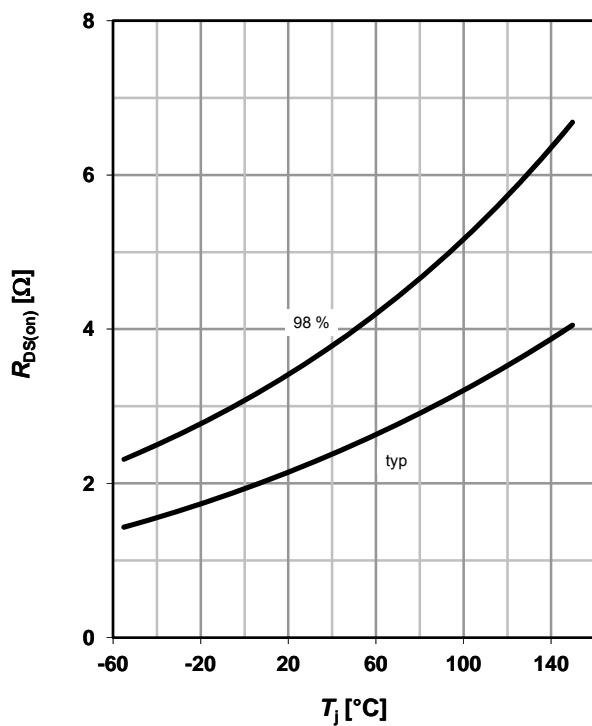

4 Max. transient thermal impedance

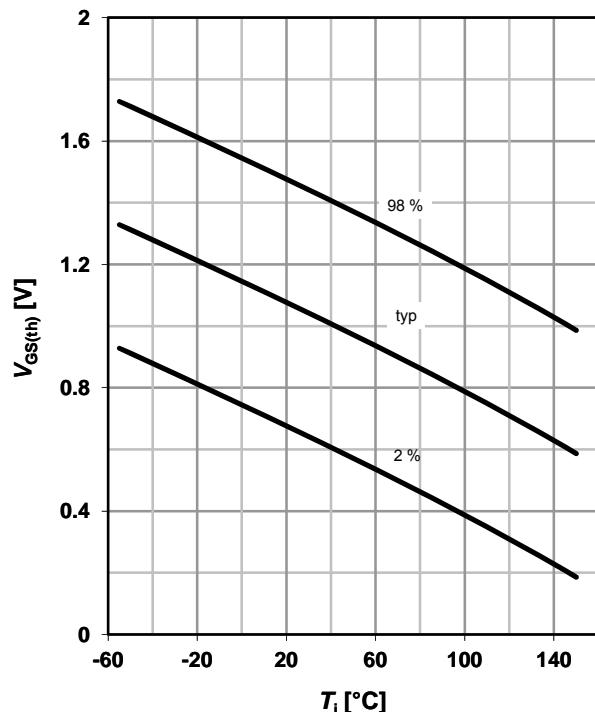
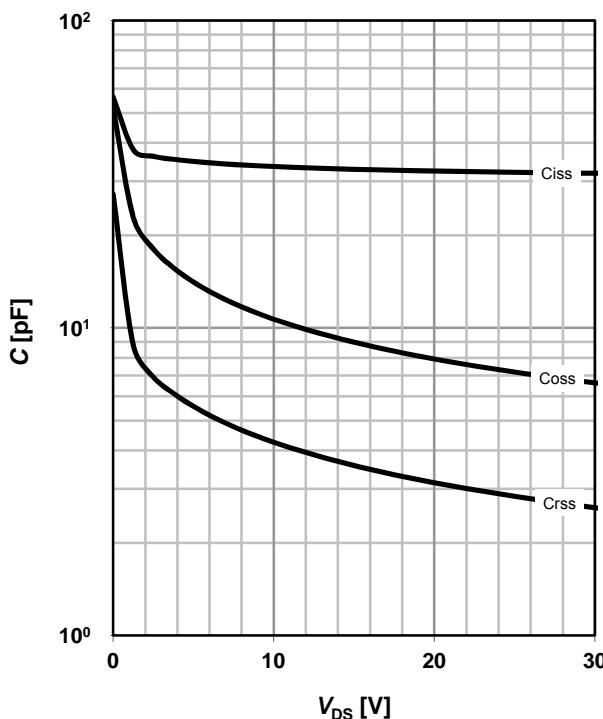
$$Z_{\text{thJA}} = f(t_p)$$

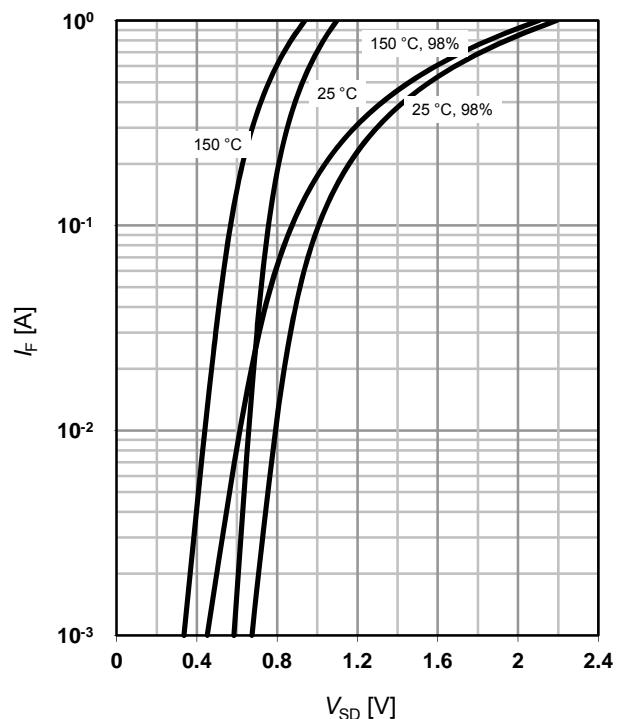
parameter: $D = t_p/T$

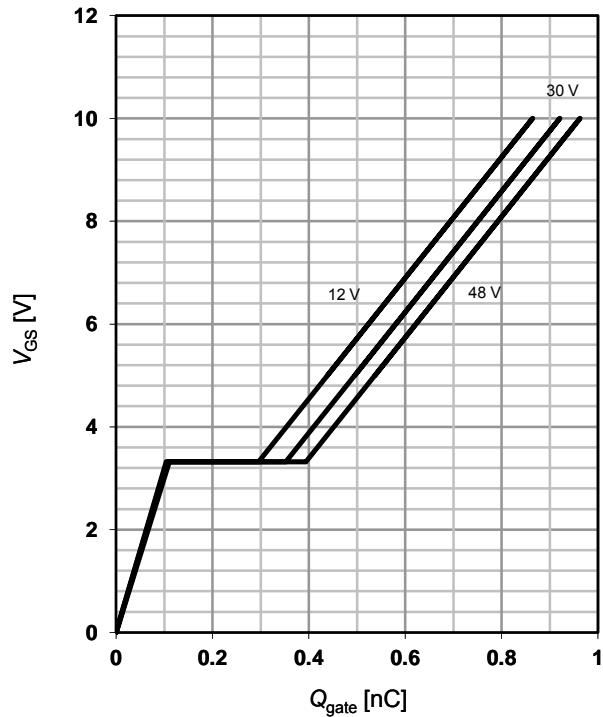
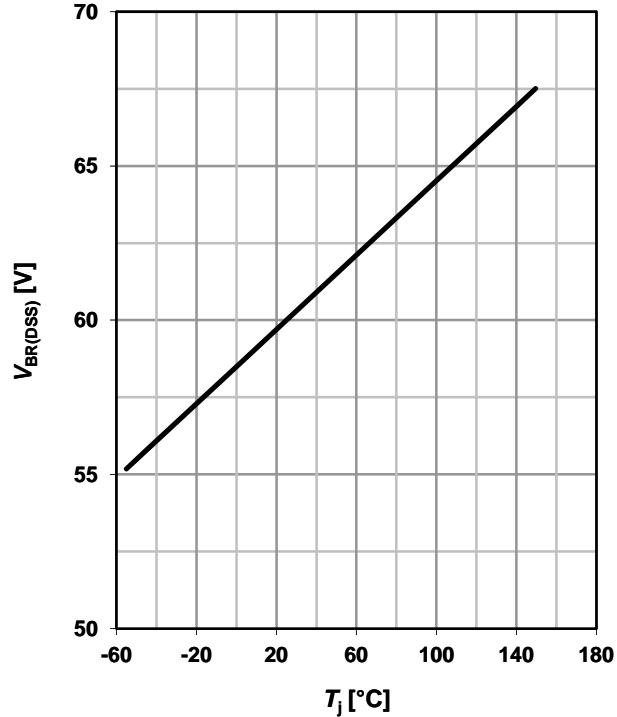


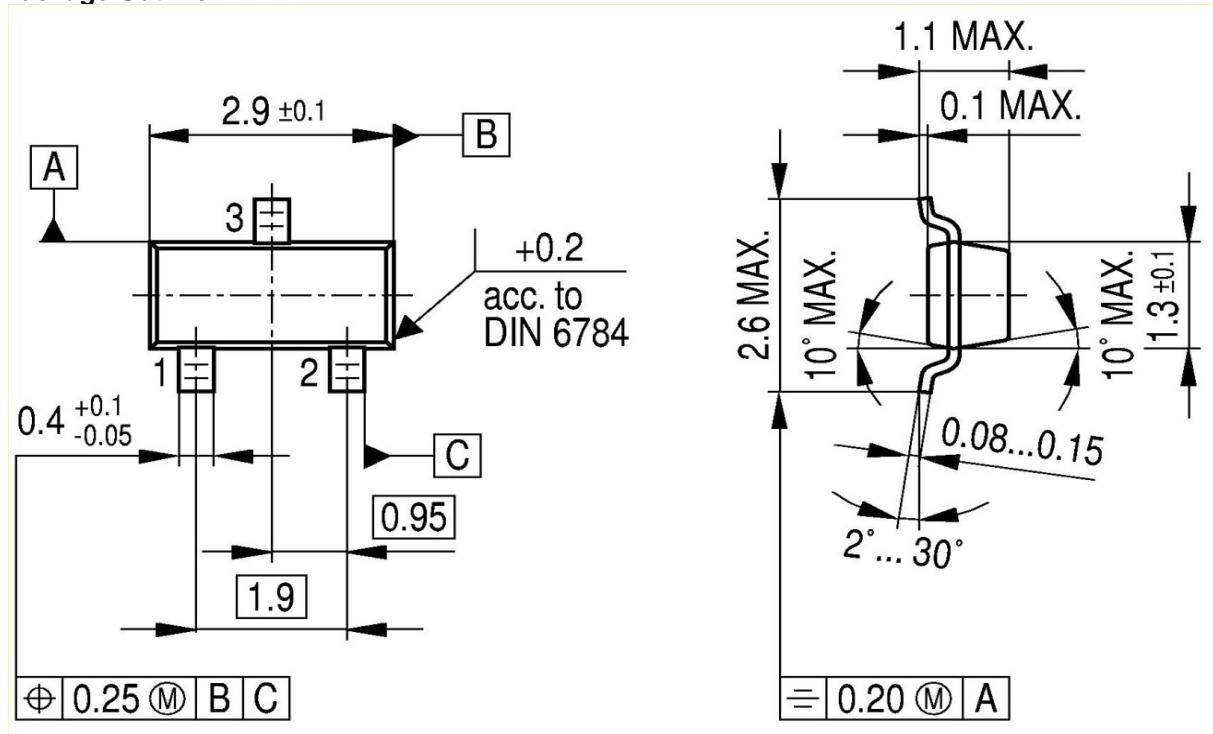
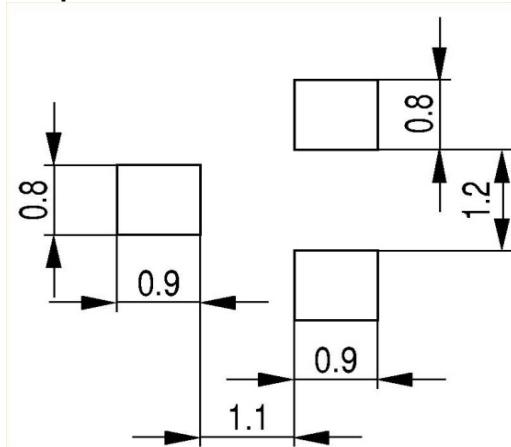
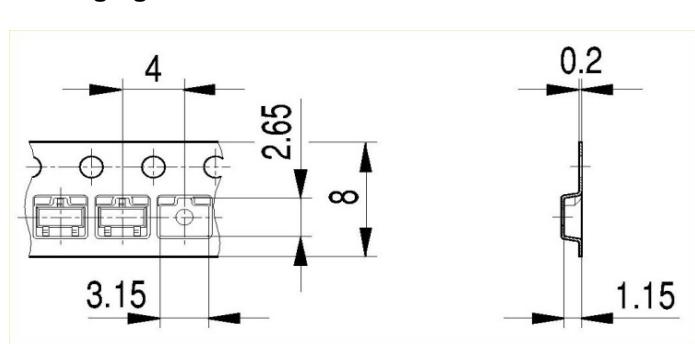
5 Typ. output characteristics
 $I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$
parameter: V_{GS} 
6 Typ. drain-source on resistance
 $R_{DS(on)} = f(I_D)$; $T_j = 25^\circ\text{C}$
parameter: V_{GS} 
7 Typ. transfer characteristics
 $I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$

8 Typ. forward transconductance
 $g_{fs} = f(I_D)$; $T_j = 25^\circ\text{C}$


9 Drain-source on-state resistance
 $R_{DS(on)} = f(T_j); I_D = 0.23 \text{ A}; V_{GS} = 10 \text{ V}$

10 Typ. gate threshold voltage
 $V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 26 \mu\text{A}$

 parameter: I_D

11 Typ. capacitances
 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25^\circ\text{C}$

12 Forward characteristics of reverse diode
 $I_F = f(V_{SD})$

 parameter: T_j


13 Typ. gate charge
 $V_{GS} = f(Q_{gate})$; $I_D = 0.23 \text{ A}$ pulsed
parameter: V_{DD} 
14 Drain-source breakdown voltage
 $V_{BR(DSS)} = f(T_j)$; $I_D = 250 \mu\text{A}$


Package Outline:

Footprint:

Packaging:


Dimensions in mm

Published by
Infineon Technologies AG
Bereich Kommunikation
St.-Martin-Straße 53
D-81541 München
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